ROLL NO.

### Code: AE53/AC53/AT53/AE103 Subject: ELECTRONIC DEVICES & CIRCUITS

# AMIETE – ET/CS/IT (Current & New Scheme)

Time: 3 Hours

# June 2018

Max. Marks: 100

PLEASE WRITE YOUR ROLL NO. AT THE SPACE PROVIDED ON EACH PAGE IMMEDIATELY AFTER RECEIVING THE QUESTION PAPER.

#### NOTE: There are 9 Questions in all.

- Question 1 is compulsory and carries 20 marks. Answer to Q.1 must be written in the space provided for it in the answer book supplied and nowhere else.
- The answer sheet for the Q.1 will be collected by the invigilator after 45 minutes of the commencement of the examination.
- Out of the remaining EIGHT Questions, answer any FIVE Questions. Each question carries 16 marks.
- Any required data not explicitly given, may be suitably assumed and stated.

#### Q.1 Choose the correct or the best alternative in the following: (2×10)

a. If 1 A current flows in a circuit, the number of electrons flowing through this circuit is (A)  $0.625 \times 10^{19}$  (B)  $1.6 \times 10^{19}$ 

(A) $0.023 \times 10$	<b>(D)</b> $1.0 \times 10$
(C) $1.6 \times 10^{-19}$	<b>(D)</b> $0.625 \times 10^{-19}$

- b. The resistance of a conductor of diameter d and length l is R Ω. If the diameter of the conductor is halved and its length is doubled, the resistance will be
  (A) R ohm
  (B) 2R ohm
  (C) 4R ohm
  (D) 8R ohm
- c. A capacitor carries a charge of 0.1 C at 5 V. Its capacitance is

   (A) 0.02 F
   (B) 0.5 F
   (C) 0.05 F
   (D) 0.2 F
- d. A 9.1-V zener diode exhibits its nominal voltage at a test current of 28 mA. At this current the incremental resistance is specified as 5 Ω. Find V<sub>Z0</sub> of the Zener model.
   (A) 8.06V

(A) 8.96V	<b>(B)</b> 9.03V
( <b>C</b> ) 9.17V	( <b>D</b> ) 9.24V

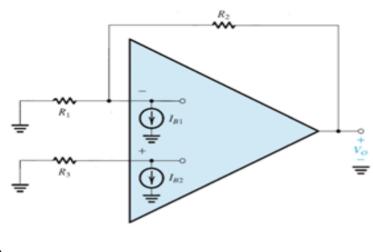
e. A shunt regulator utilizing a zener diode with an incremental resistance of 5  $\Omega$  is fed through an 82- $\Omega$  resistor. If the raw supply changes by 1.0 V, what is the corresponding change in the regulated output voltage?

( <b>A</b> ) 72.7 mV	<b>(B)</b> 73.7 mV
(C) 74.7 mV	( <b>D</b> ) 75.7 mV

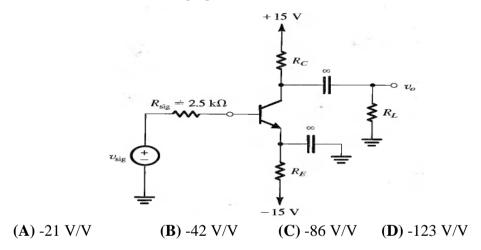
f. The circuit is to operate at a temperature in the range 0°C to 75°C and the temperature coefficient of V<sub>OS</sub> is 10 μV/°C?
(A) 8.5 mV
(B) 9 mV
(C) 9.5 mV
(D) 10 mV

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- g. Consider the circuit shown below which reduces the impact of the input bias current. If  $I_{B1} = I_{B2} =$  Input bias current, then determine the value of  $R_3$  so that the output voltage (v<sub>0</sub>) is not impacted by the input bias current.
  - (A) (R1 R2)/(R1+R2)
    (B) (R1 R2)/(R1-R2)
    (C) R1-(R1 R2)/(R1+R2)
    (D) R2- (R1 R2)/(R1+R2)



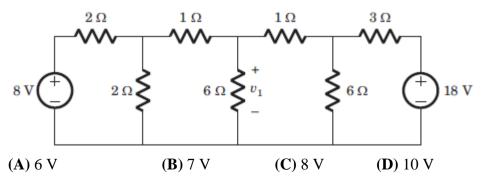
h. The circuit shown below is applied with small sine wave signal having zero average. The transistor  $\beta = 100$ . For R(L) = 10 k $\Omega$  and transistor Ro = 200 k $\Omega$ , determine the overall voltage gain.



A battery has a short-circuit current of 30 A and an open circuit voltage of 24 V. If the battery is connected to an electric bulb of resistance 2 ohm, the power dissipated by the bulb is

(A) 80 W (B) 1800 W (C) 112.5 W (D) 228 W

j. For the following circuit, determine the value of  $v_1$ 

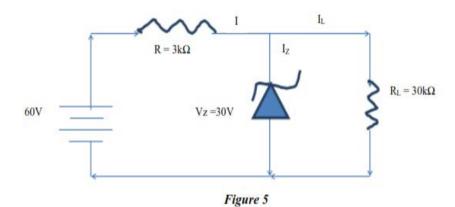


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#### Answer any FIVE Questions out of EIGHT Questions Each question carries 16 marks

- **Q.2** a. Define  $\alpha_{dc}$  and  $\beta_{dc}$  of BJT. Derive the relation between these two parameters. (5)
  - **b.** A BJT with measured current levels of  $I_C = 16mA$ ,  $I_E = 16.04 \text{ mA}$  is replaced with another BJT which has  $\beta_{dc} = 25$ . Calculate the new level of  $I_C$  and  $I_E$  assuming that the base current remains constant. (5)
  - c. Why biasing is required in BJT circuit? Draw the circuit of different biasing arrangements available. (6)
- Q.3 a. Draw the circuits and the corresponding waveforms of half wave, bridge, centre tap full wave rectifiers and discuss the working principle of these circuits. (12)
  - b. What is transconductance? Prove  $g_m = g_{mo} (I_D / I_{DSS})^{\frac{1}{2}}$ , where the terms denote their original meaning. (4)
- **Q.4** a. Calculate the current through Zener diode if the load resistance  $RL = 30 k\Omega$  for the circuit given below (Figure 5): (6)



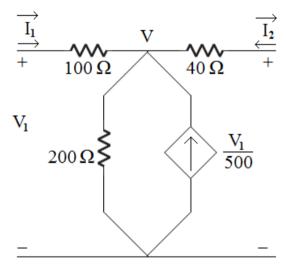
- b. Calculate the resistivity of Si at 300K, if donor impurity to the extent of 1 part in 10<sup>8</sup> atoms of Si is added, find the density of minority carriers and the resistivity.
- c. Explain the concept of Tunnel diode and Schottky Diode with the help of their I-V characteristic. (5)
- Q.5 a. Explain the concept of Cascade amplifier with the help of its circuit diagram. Also, define its applications. (8)
  - b. Explain working of single stage RC coupled amplifier. (8)

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- Q.6 a. Sketch the circuit diagram of a Class B push-pull power amplifier using transformer-coupling. Derive relation for its dc input power, ac output power and the efficiency.
  - b. Sketch Class A transformer coupled amplifier. In this circuit, if transistor used has power dissipation (PD) =10W. (i) What maximum signal output power it can produce under ideal conditions? (ii) If two such identical transistors are used in Class B push pull amplifier, what maximum signal output this transistor pair can produce under ideal condition? (8)
- Q.7 a. What are the basic laws of the Circuit Theory? On what principle are they based? (8)
  - b. Distinguish between natural and forced response of an RC Circuit.
     Determine the y-parameters of the network of figure given and then draw its equivalent circuit accordingly.
     (8)



- **Q.8** a. Draw and explain the operation of a Phase shift oscillator.
  - b. Draw the circuit of a Wien-bridge oscillator using Op-Amp and describe its working. Find an expression for the frequency of oscillation. (3+5)
- Q.9 a. Explain the various steps involved in IC fabrication. Explain ion implantation IC fabrication technique and also write its advantages. (4+4+2)
  - b. Explain the Oxidation and Photolithography process with diagram for device fabrication. (6)

(8)